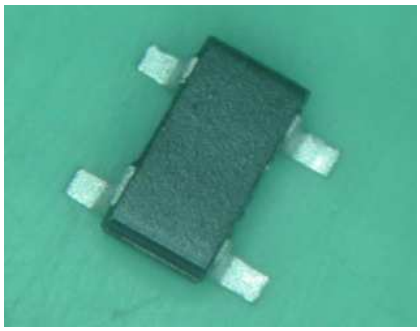
素子 GaAs

MODEL

GA201



	Icmax	15(at25℃)	mA
	Pmax	150	mW
	Topr	−40～125	℃
	Tstg	−55～150	℃

用 途

T=25

	VH ※2	Vc=1V B=100mT	24	28	33	mV
	Vo% ※1	Vc=1V B=0mT	−15		15	%
	Rin	I=1mA	650	800	1000	Ω
	Rout	I=1mA		1800	3000	Ω
	αVH	B=100mT Ic=5mA T1=25℃, T2=125℃			−0.06	%/℃
	β Rin	B=0mT Ic=0.1mA T1=25℃, T2=125℃			0.3	%/℃
性度偏差	γ	Ic=5m， B1=1KG， B2=5KG			2	%

※1：Vo(%)=(Vo/VH)×100　　※2：VH=VHM−Vo

αVH = [1/VH(T1)] × [VH(T1)-VH(T2)] × [1/(T1-T2)] ×100

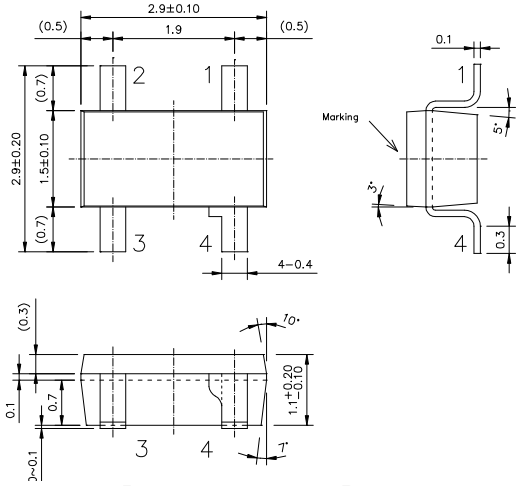
β Rin = [1/Rin(T1)] × [Rin(T1)-Rin(T2)] × [1/(T1-T2)] ×100

γ =(KH2-KH1)/[(KH1+KH2)/2] ×100

KH1=VH(B1)/(Ic×B1) ； KH2=VH(B2)/(Ic×B2)

HF

GA201 HF



Pin1: 入＋　　**Pin3**: 入－

Pin2: 出＋　　**Pin4**: 出－

		%	
GA201	A	−5～+5	
	B	−5～−10 +5～+10	Vo(%)=(Vo/VH)×100
	C	−10～−15 +10～+15	Vo :Vc=1V B=0mT
			VH Vc=1V B=100mT
			(at25℃)

GA201		3000pcs	15000pcs(5)